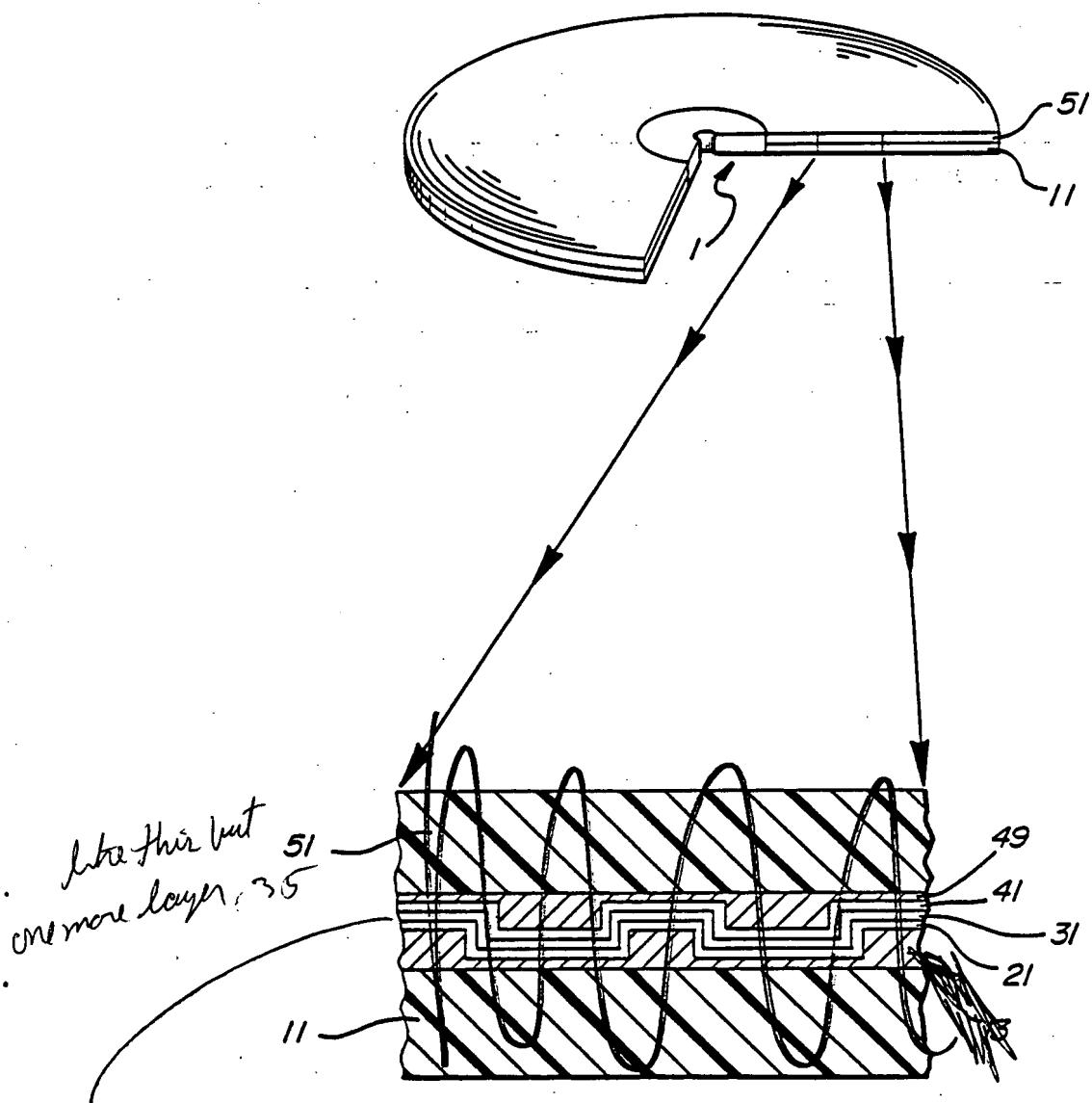
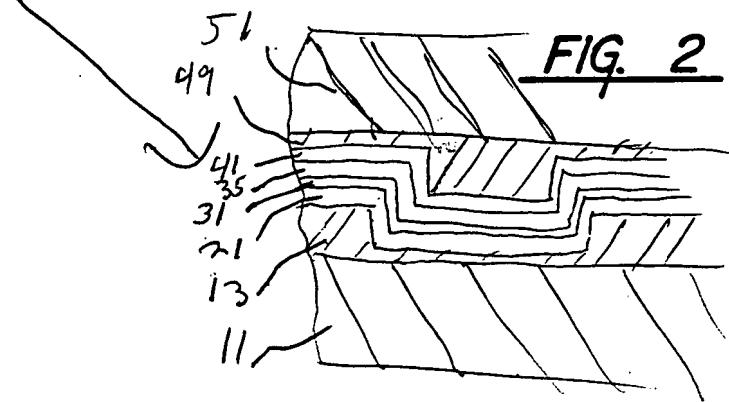


FIG. 1FIG. 2

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WRITE ONCE SEQUENCE

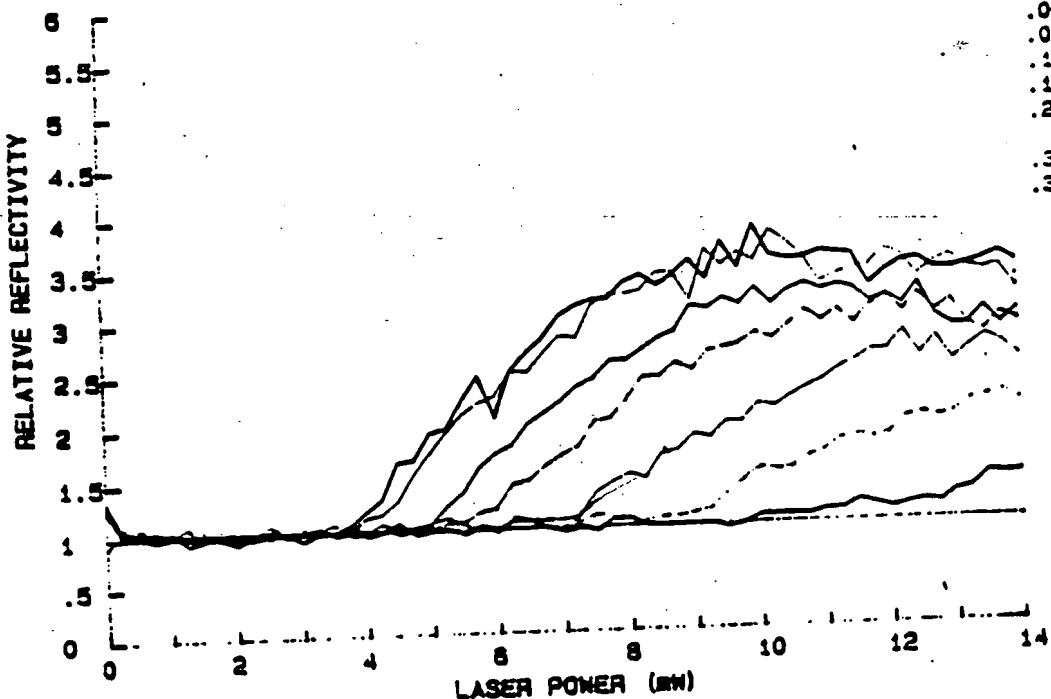
SAMPLE NO: E-1048

DATE: 3/21/89

Te53Ge37Sb10/Sb

CRYSTALLIZATION PULSE WIDTH:

.025US
.05 US
.075US
.10 US
.15 US
.20 US
.30 US
.35 US



3
Figure ~~10~~

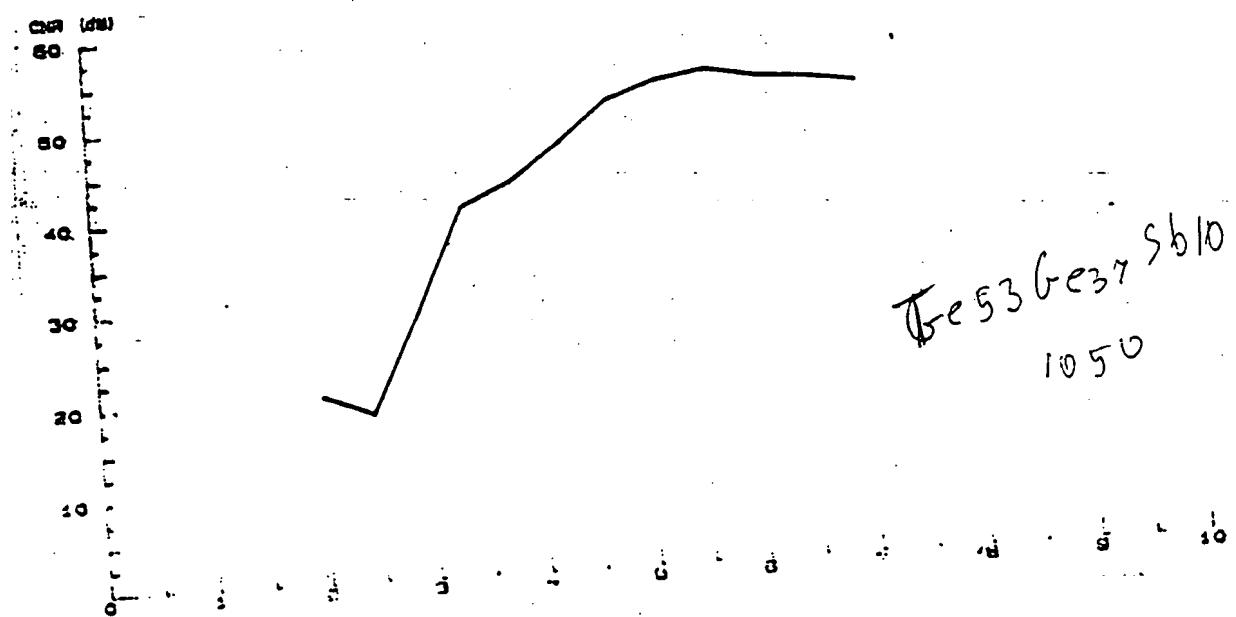
07/657170

CARRIER TO NOISE RATIO
VS
RECORD POWER

SP: : E-1050
RECORDING : Te: Ge: Sb/Sb
: unsealed disc
D: : 24 Mar 1989

RECORD FREQUENCY: 3.86 KHz

INITIALIZED 0 CYCLES 10% 10 KHz



Te₅₃ Ge₃₇ Sb₁₀
10⁵⁰

4

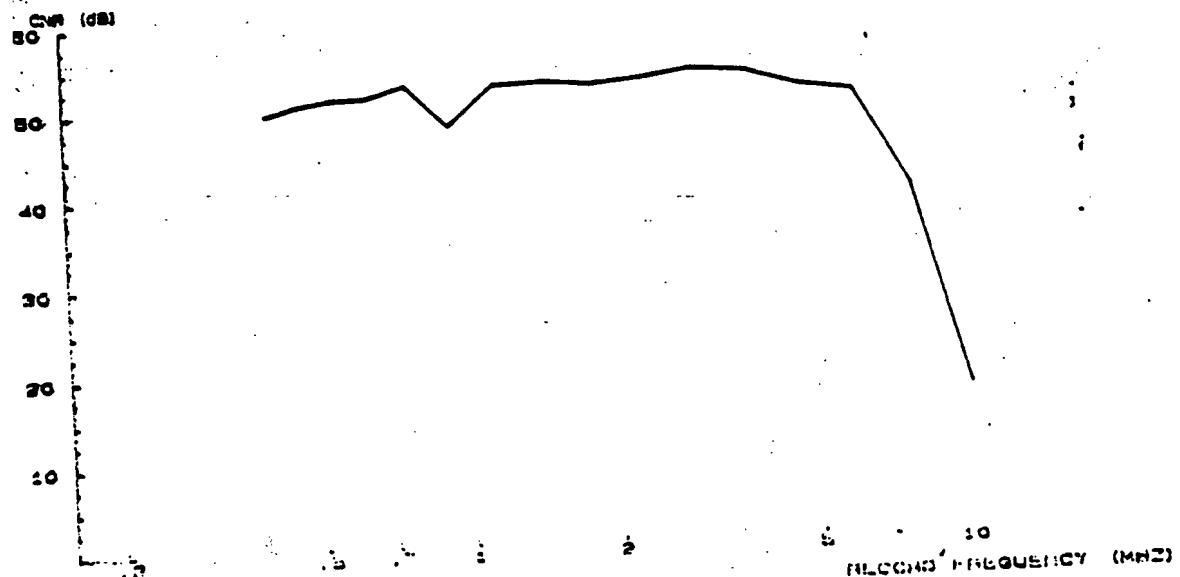
Figure 40

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CARRIER-TO-NOISE RATIO
1.5
(RECORD) : 70.5001150

SEARCH NO : E-1050
DESCRIPTION : Te: Ge: Sb/Sb
: unsealed disc
DATE : 24 Mar 1989

RECORD POWER: 5.5 mW
INITIALIZED 0 CYCLES 170 10 V.c



5
Figure 24

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Rate vs Time

Te Ge Sb alloy source (50: 41: 9)

4/12/89

E-1072 520 C

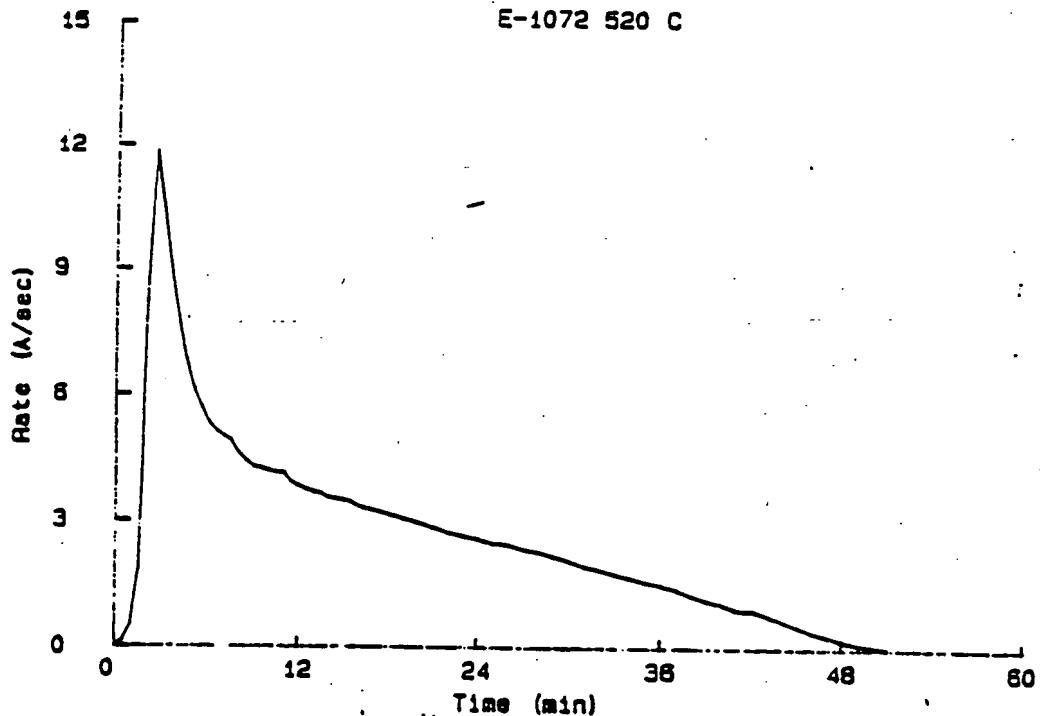


Figure 22

07/657170

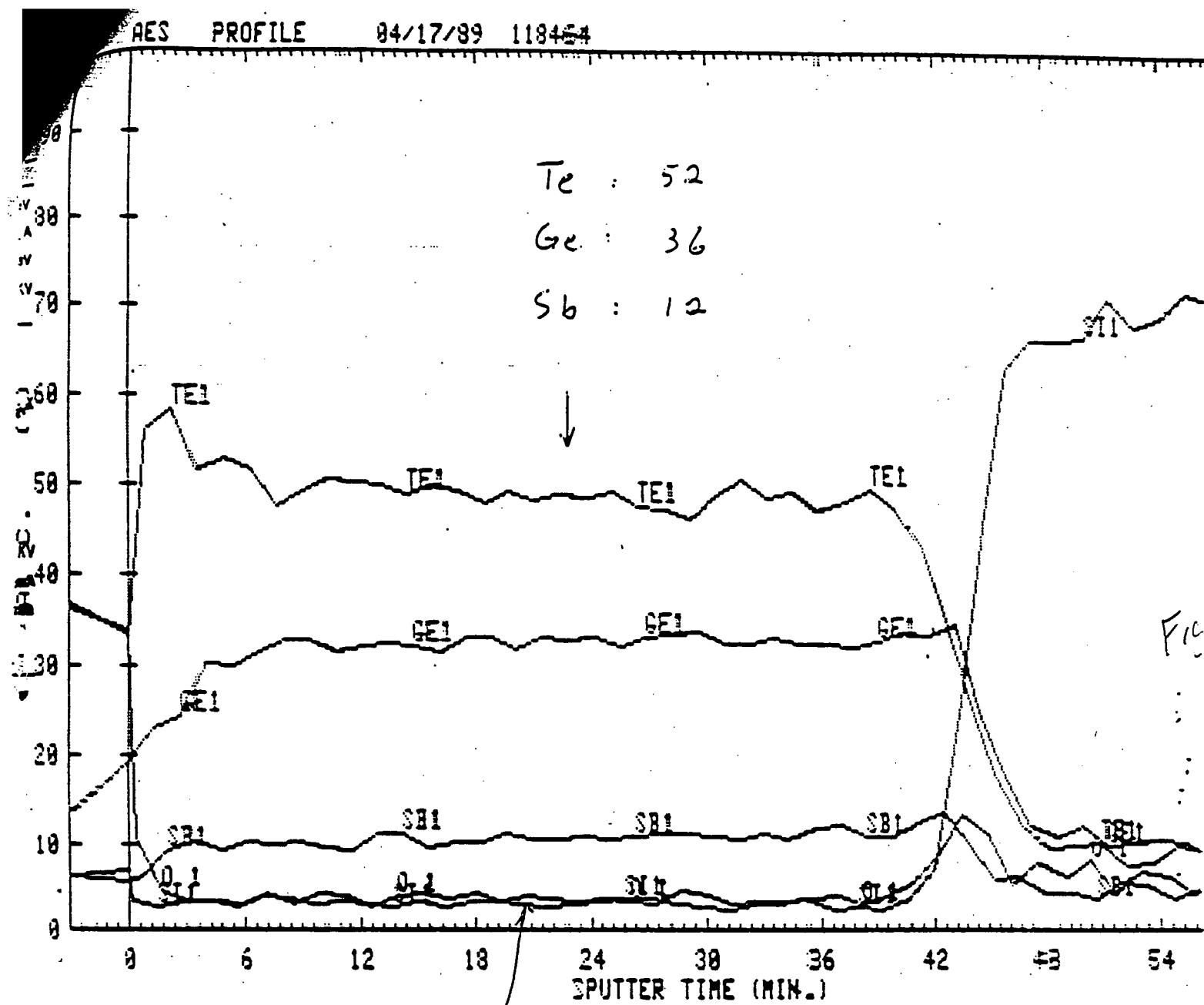
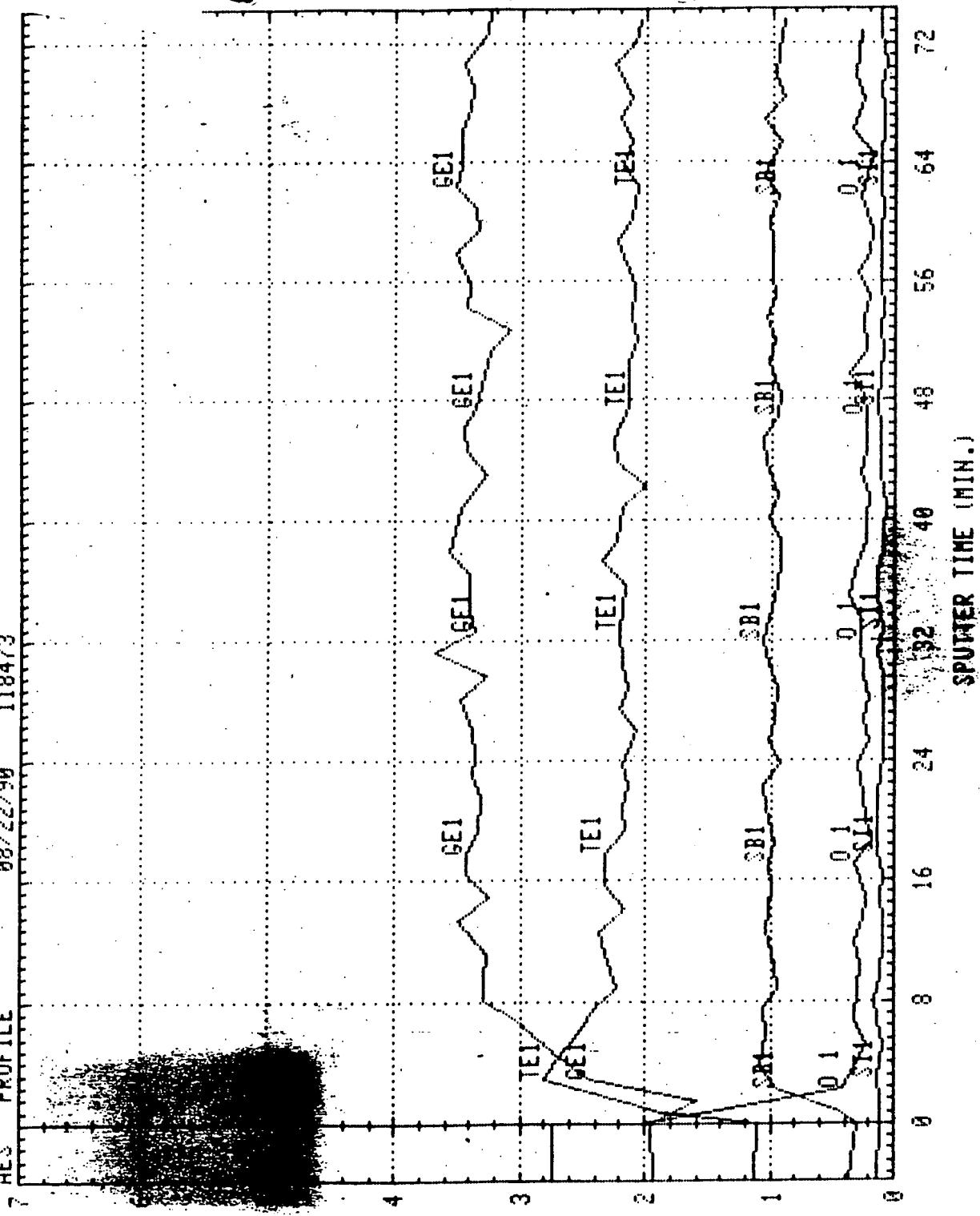


Figure 33

657170

AES PROFILE 03/22/90 118473



657170
SAMPLE # 118473
OBJECT # 3
V (1) 1.5 mA
V (2) 3
V (100) 0.4 KV
V (1000) 1.4 KV
DEPTH A WRIT
C SURVEY SCAN
□ SPOT REL MAG BREAK
□ TV SPUTTER
□ W W/O
□ DEPTH PROFILE
PUTTER CONDITIONS 11.5 KV
(1) 3.5 mA
(MISSION) 3 mm
MASTER 3 mm
PUTTER RATE 14.20 fm/min
WRIT 14.20 fm/min

Par w/ 657170
Fig 6

TE51 Cee40 S69

657170

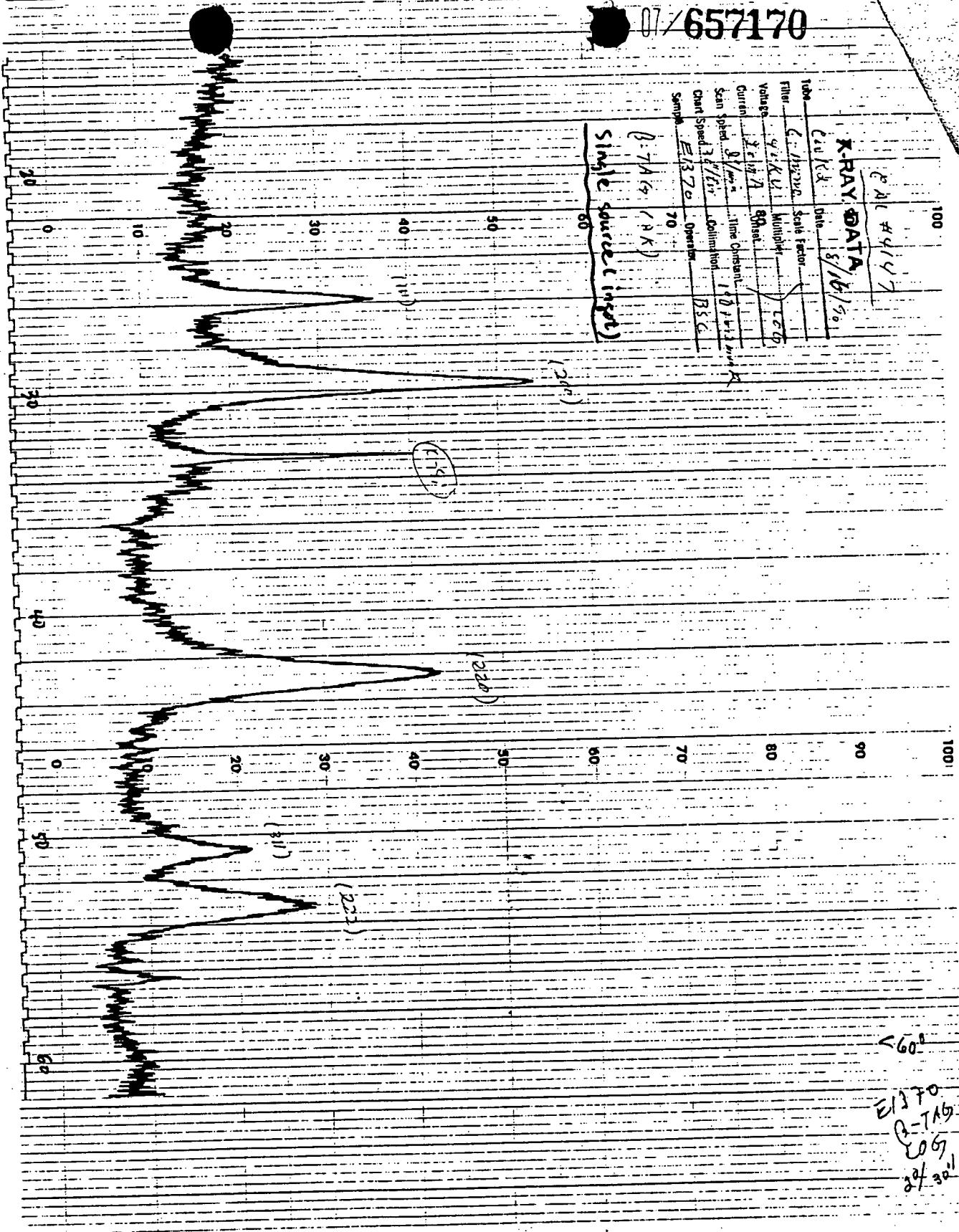


Fig 9